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**AMENDMENTS TO CLAIMS**

Claims 1-17 (Cancelled)

18. (Currently amended) An information storage device comprising an array of memory cells, each memory cell including at least one magnetic tunnel junction, each magnetic tunnel junction including a data layer and a [soft] ferrimagnet reference layer that is softer than the data layer, the data and ferrimagnet reference layers having magnetizations that can be switched between first and second directions during write operations, only the ferrimagnet reference layers [layer] being switchable between first and second directions during read operations.

19. (Previously presented) The device of claim 18, wherein each reference layer includes first and second ferromagnetic layers separated by an electrically conductive and magnetically non-conductive spacer layer.

20. (Previously presented) The device of claim 19, wherein reference layer coercivity is determined by the ratio of first ferromagnetic layer thickness to second ferromagnetic layer thickness.

21. (Previously presented) The device of claim 19, wherein magnetic moments of the first and second ferromagnetic layers of a ferrimagnet reference layer substantially cancel out.

22. (Cancelled)

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23. (Previously presented) The device of claim 18, further comprising pluralities of word and bit lines for the array of memory cells; and a plurality of read lines for the memory cells.